

### ABSTRACT OF THE DISCLOSURE

The TFT electric characteristic is ready to be influenced by the channel region in the neighborhood of an interface between a semiconductor and a gate insulating film. The present invention provides TFTs reduced in electric 5 characteristic deviations and a method for manufacturing the same. The invention forms a region or layer containing an inactive element, or rear gas element, in the channel region. As shown in FIG. 1, a rear gas element is contained at least in an upper layer of the channel region.